

Erratum

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Erratum: "Ion-channeling analysis of boron clusters in silicon" [J. Appl. Phys. 90, 4741 (2001)]

L. J. M. Selen, F. J. J. Janssen, L. J. van IJzendoorn,^{a)} and M. J. A. de Voigt
Research Institutes CPS and COBRA, Cyclotron Laboratory, Department of Applied Physics, Eindhoven University of Technology, P.O. Box 513, 5600 MB Eindhoven, The Netherlands

M. J. J. Theunissen
Phillips Research Laboratories, Eindhoven, The Netherlands

P. J. M. Smulders
Materials Science Center, University of Groningen, Groningen, The Netherlands

T. J. Eijkemans
Research School Cobra, Department of Applied Physics, Eindhoven University of Technology, Eindhoven, The Netherlands

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The title of the paper should have been: "Ion channeling for strain analysis in buried nanofilms (<6 nm)." In addition, three references appeared incorrectly; corrected versions of Refs. 1, 7, and 13 follow:

¹B. D. Cullity, *Elements of X-Ray Diffraction* (Addison-Wesley, Reading, MA, 1976).

⁷T. C. Q. Noakes, P. Baily, P. K. Hucknall, K. Donovan, and M. A. Howson, *Phys. Rev. B* **58**, 4934 (1998).

¹³J. Lindhard and K. Dan., *Vidensk. Selsk. Mat. Fys. Medd.* **1965**, 34.

^{a)}Author to whom correspondence should be addressed. Present address: Cyclotron Laboratory, Department of Applied Physics, Eindhoven University of Technology, P.O. Box 513, 5600 MB Eindhoven, The Netherlands; electronic mail: L.J.van.IJzendoorn@tue.nl.